

February 2010

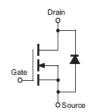
# 2N7002W

# **N-Channel Enhancement Mode Field Effect Transistor**

## **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- · Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- · Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant





## **Absolute Maximum Ratings \*** $T_A = 25$ °C unless otherwise noted

Symbol	Parameter		Value	Units	
V <sub>DSS</sub>	Drain-Source Voltage		60	V	
$V_{DGR}$	Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		60	V	
$V_{GSS}$	Gate-Source Voltage	Continuous Pulsed	±20 ±40	V	
I <sub>D</sub>	Drain Current	Continuous Continuous @ 100°C Pulsed	115 73 800	mA	
$T_{J}$ , $T_{STG}$	Junction and Storage Temperature Range		-55 to +150	°C	

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

## **Thermal Characteristics**

Symbol	Parameter	Value	Units	
P <sub>D</sub>	Total Device Dissipation Derating above T <sub>A</sub> = 25°C	200 1.6	mW mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient *	625	°C/W	

<sup>\*</sup> Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

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# **Electrical Characteristics** $T_A = 25$ °C unless otherwise noted

Parameter	Test Condition	Min.	Тур.	Max.	Units
teristics (Note1)					
Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =10uA	60	78	-	V
Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V V <sub>DS</sub> =60V, V <sub>GS</sub> =0V, @T <sub>C</sub> =125°C	-	0.001 7	1.0 500	μΑ
Gate-Body Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	0.2	±10	nA
teristics (Note1)					
Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.0	1.76	2.0	V
Static Drain-Source On-Resistance	V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A, V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A, @T <sub>J</sub> =125°C	-	1.6 2.53	7.5 13.5	Ω
On-State Drain Current	V <sub>GS</sub> =10V, V <sub>DS</sub> =7.5V	0.5	1.43	-	Α
Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =0.2A	80	356.5	-	mS
Characteristics					
Input Capacitance		-	37.8	50	pF
Output Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz	-	12.4	25	pF
Reverse Transfer Capacitance		-	6.5	7.0	pF
Characteristics			•	•	
Turn-On Delay Time	V <sub>DD</sub> =30V, I <sub>D</sub> =0.2A, V <sub>GEN</sub> =10V	-	5.85	20	no
Turn-Off Delay Time	$R_L=150\Omega$ , $R_{GEN}=25\Omega$	-	12.5	20	ns
	teristics (Note1)  Drain-Source Breakdown Voltage Zero Gate Voltage Drain Current  Gate-Body Leakage teristics (Note1)  Gate Threshold Voltage Static Drain-Source On-Resistance On-State Drain Current Forward Transconductance Characteristics  Input Capacitance Output Capacitance Reverse Transfer Capacitance Characteristics  Turn-On Delay Time	teristics (Note1)         Drain-Source Breakdown Voltage       V <sub>GS</sub> =0V, I <sub>D</sub> =10uA         Zero Gate Voltage Drain Current       V <sub>DS</sub> =60V, V <sub>GS</sub> =0V, @T <sub>C</sub> =125°C         Gate-Body Leakage       V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V         teristics (Note1)       V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA         Static Drain-Source       V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A, @T <sub>J</sub> =125°C         On-Resistance       V <sub>GS</sub> =10V, V <sub>DS</sub> =7.5V         Forward Transconductance       V <sub>DS</sub> =10V, I <sub>D</sub> =0.2A         Characteristics       Input Capacitance         Output Capacitance       V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz         Reverse Transfer Capacitance       V <sub>DD</sub> =30V, I <sub>D</sub> =0.2A, V <sub>GEN</sub> =10V         Characteristics       Turn-On Delay Time	Drain-Source Breakdown Voltage   V <sub>GS</sub> =0V, I <sub>D</sub> =10uA   60     Zero Gate Voltage Drain Current   V <sub>DS</sub> =60V, V <sub>GS</sub> =0V   - V <sub>DS</sub> =60V, V <sub>GS</sub> =0V, V <sub>DS</sub> =60V, V <sub>DS</sub> =60V, V <sub>DS</sub> =0V   -     Gate-Body Leakage   V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V   -     teristics (Note1)     Gate Threshold Voltage   V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA   1.0     Static Drain-Source   V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A,	Drain-Source Breakdown Voltage   V <sub>GS</sub> =0V, I <sub>D</sub> =10uA   60   78     Zero Gate Voltage Drain Current   V <sub>DS</sub> =60V, V <sub>GS</sub> =0V   - 0.001     V <sub>DS</sub> =60V, V <sub>GS</sub> =0V, @T <sub>C</sub> =125°C   7     Gate-Body Leakage   V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V   - 0.2     teristics (Note1)     Gate Threshold Voltage   V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA   1.0   1.76     Static Drain-Source   V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A,	Drain-Source Breakdown Voltage   V <sub>GS</sub> =0V, I <sub>D</sub> =10uA   60   78   -

Note1: Short duration test pulse used to minimize self-heating effect.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

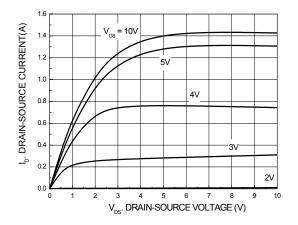


Figure 3. On-Resistance Variation with Temperature

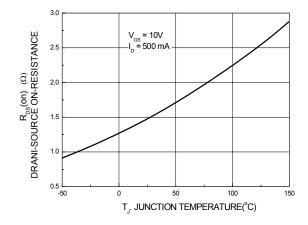


Figure 5. Transfer Characteristics

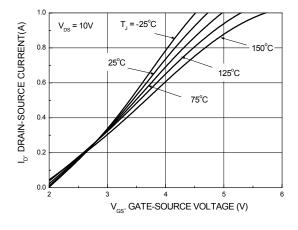


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

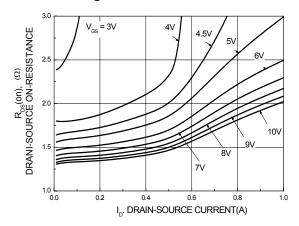


Figure 4. On-Resistance Variation with Gate-Source Voltage

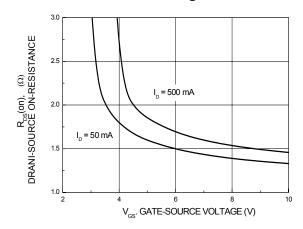
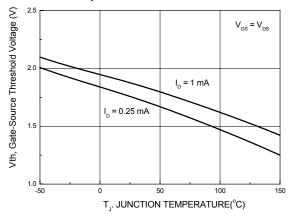


Figure 6. Gate Threshold Variation with Temperature



# **Typical Performance Characteristics**

Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

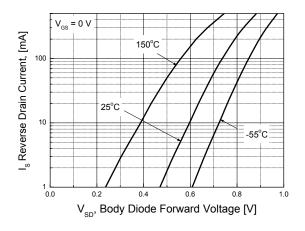
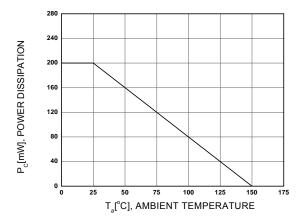
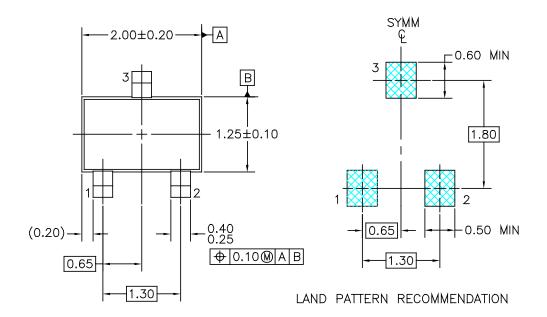


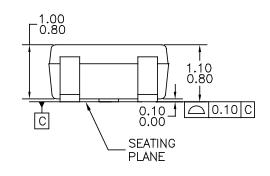
Figure 8. Power Derating

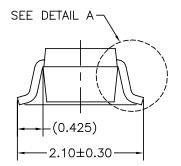


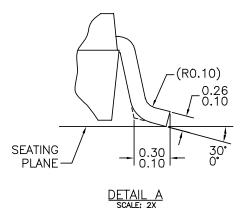
# **Package Dimensions**

## **SOT323**









NOTES: UNLESS OTHERWISE SPECIFIED

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